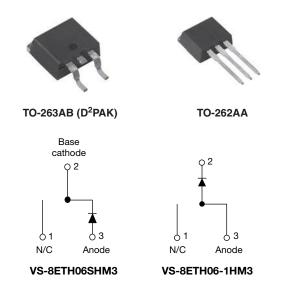
# VS-8ETH06SHM3, VS-8ETH06-1HM3



**Vishay Semiconductors** 

### Hyperfast Rectifier, 8 A FRED Pt<sup>®</sup>



PRODUCT SUMMARY								
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA							
I <sub>F(AV)</sub>	8 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub>	1.3 V							
t <sub>rr</sub> typ.	18 ns							
T <sub>J</sub> max.	175 °C							
Diode variation	Single die							

#### **FEATURES**

- · Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- AEC-Q101 qualified, meets JESD 201, class 1 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS						
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	8							
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	90	А						
Peak repetitive forward current	I <sub>FM</sub>		16							
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A -		2.0	2.4	V			
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8				
Poverao lookogo ourrent	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	0.3	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	55	500	μA			
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	17	-	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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# VS-8ETH06SHM3, VS-8ETH06-1HM3

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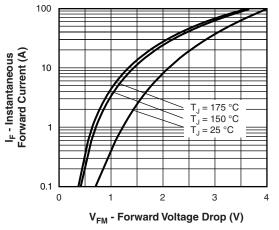
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 A$ , $dI_F/dt = 1$	00 A/µs, V <sub>R</sub> = 30 V	-	18	22				
	+	$I_F = 8 A, dI_F/dt = 1$	00 A/µs, V <sub>R</sub> = 30 V	-	20	-				
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns			
		T <sub>J</sub> = 125 °C		-	40	-				
Deck recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 8 A$	-	2.4	-	A			
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 390 V	-	4.8	-				
	0	T <sub>J</sub> = 25 °C		-	25	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	nc			
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 600 A/µs	-	12	-	А			
Reverse recovery charge	Q <sub>rr</sub>	]	V <sub>R</sub> = 390 V	-	220	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C				
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	1.4	2					
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	-				
Maight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-263AB (D <sup>2</sup> PAK) 8ETH065								
Marking device		Case style TO-262AA	8ETH06-1H							

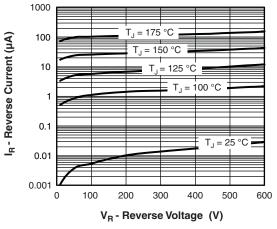
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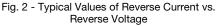
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Fig. 1 - Maximum Forward Voltage Drop Characteristics





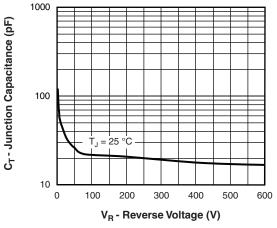


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

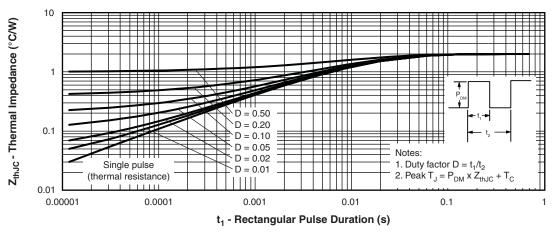
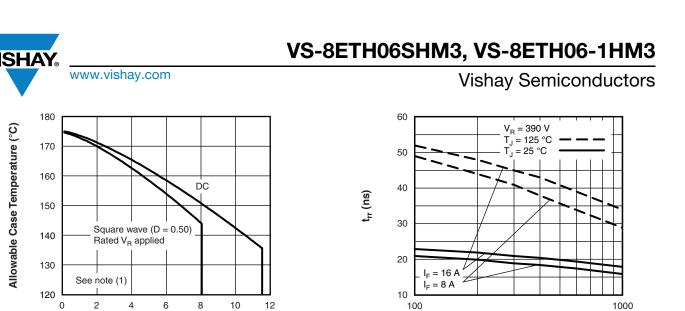
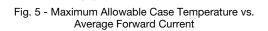


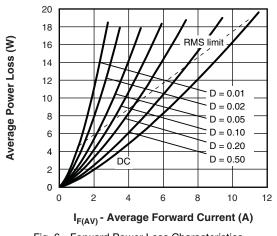
Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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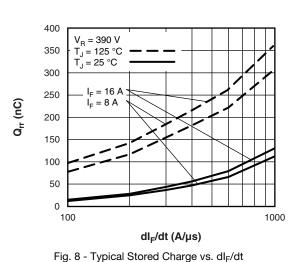




I<sub>F(AV)</sub> - Average Forward Current (A)





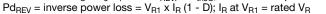


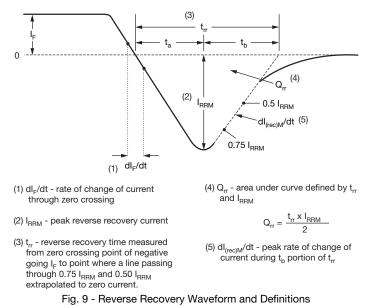
dl<sub>F</sub>/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt



Note (1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ; Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at ( $I_{F(AV)}/D$ ) (see fig. 6);





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#### **ORDERING INFORMATION TABLE**

Device code	VS-	8	Е	т	н	06	s	TRL	н	М3		
		2	(3)	4	5	(6)	(7)	(8)	(9)	(10)		
	1 - Vishay Semiconductors product											
	2											
		. Т=	TO-220	, D <sup>2</sup> PAł	<							
	5	. H=	hyperfa	st rectif	ier							
	6	- Volt	age rati	ng (06 =	= 600 V)							
	7.	• S	= D <sup>2</sup> PA	К								
		• -1	= TO-2	62								
	8	• N	• None = tube (50 pieces)									
		• TI	<ul> <li>TRL = tape and reel (left oriented, for D<sup>2</sup>PAK package)</li> </ul>									
		• TI	<ul> <li>TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)</li> </ul>									
	9.	• H=	AEC-Q	101 qua	lufied							
	<b>10</b> ·	· МЗ	= halog	en-free,	RoHS-o	complia	nt, and	terminat	tions lea	ad (Pb)-f		

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-8ETH06SHM3	50	1000	Antistatic plastic tube						
VS-8ETH06STRRHM3	800	800	13"diameter reel						
VS-8ETH06STRLHM3	800	800	13"diameter plastic reel						
VS-8ETH06-1HM3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95046					
Dimensions	TO-262AA	www.vishay.com/doc?95419					
Part marking information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95444					
Part marking information	TO-262AA	www.vishay.com/doc?95443					
Packaging information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95032					

### **Outline Dimensions**



D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 08-Jul-15

1

### **Outline Dimensions**



**Vishay Semiconductors** 

**TO-262** 

#### **DIMENSIONS** in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 \_ 1.65 0.065 3 \_ 3.36 0.132 0.146 L2 3.71

3. - Anode

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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